

Koji Muraki

List of Publications by Year in descending order

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195
papers

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citations

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195
docs citations

195
times ranked

2703
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface segregation of In atoms during molecular beam epitaxy and its influence on the energy levels in InGaAs/GaAs quantum wells. Applied Physics Letters, 1992, 61, 557-559.	3.3	450
2	Controlled multiple quantum coherences of nuclear spins in a nanometre-scale device. Nature, 2005, 434, 1001-1005.	27.8	186
3	Electrically Controlled Nuclear Spin Polarization and Relaxation by Quantum-Hall States. Physical Review Letters, 2002, 88, 176601.	7.8	146
4	Unraveling the Spin Polarization of the $\hat{1}/2 = 5/2$ Fractional Quantum Hall State. Science, 2012, 335, 828-831.	12.6	145
5	Quantum dot molecules. Physica B: Condensed Matter, 1998, 249-251, 206-209.	2.7	129
6	Gate-dependent spin-orbit coupling in multielectron carbon nanotubes. Nature Physics, 2011, 7, 348-353.	16.7	122
7	Edge channel transport in the InAs/GaSb topological insulating phase. Physical Review B, 2013, 87, .	3.2	119
8	Fractionalized wave packets from an artificial Tomonaga-Luttinger liquid. Nature Nanotechnology, 2014, 9, 177-181.	31.5	107
9	Dissociation of Vertical Semiconductor Diatomic Artificial Molecules. Physical Review Letters, 2001, 87, 066801.	7.8	73
10	Waveform measurement of charge- and spin-density wavepackets in a chiral Tomonaga-Luttinger liquid. Nature Physics, 2017, 13, 559-562.	16.7	69
11	Surface segregation of In atoms and its influence on the quantized levels in InGaAs/GaAs quantum wells. Journal of Crystal Growth, 1993, 127, 546-549.	1.5	68
12	Charge Excitations in Easy-Axis and Easy-Plane Quantum Hall Ferromagnets. Physical Review Letters, 2001, 87, 196801.	7.8	65
13	Molecular phases in coupled quantum dots. Physical Review B, 2004, 69, .	3.2	58
14	Voltage-controlled group velocity of edge magnetoplasmon in the quantum Hall regime. Physical Review B, 2010, 81, .	3.2	58
15	Ballistic transport in induced one-dimensional hole systems. Applied Physics Letters, 2006, 89, 092105.	3.3	55
16	Spin Degree of Freedom in the $\hat{1}/2=1$ Bilayer Electron System Investigated by Nuclear Spin Relaxation. Physical Review Letters, 2005, 94, 096802.	7.8	53
17	Room-temperature stability of Pt nanogaps formed by self-breaking. Applied Physics Letters, 2009, 94, .	3.3	52
18	Low-Frequency Spin Dynamics in a Canted Antiferromagnet. Science, 2006, 313, 329-332.	12.6	50

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19	NMR profiling of quantum electron solids in high magnetic fields. Nature Physics, 2014, 10, 648-652.	16.7	50
20	Spin polarization of fractional quantum Hall edge channels studied by dynamic nuclear polarization. Physical Review B, 2002, 65, .	3.2	49
21	Plasmon transport in graphene investigated by time-resolved electrical measurements. Nature Communications, 2013, 4, 1363.	12.8	46
22	NMR Evidence for Spin Canting in a Bilayer $\nu = 2$ Quantum Hall System. Physical Review Letters, 2007, 99, 076805.	7.8	42
23	Two-dimensional electron gas formed in a back-gated undoped heterostructure. Applied Physics Letters, 1998, 72, 1745-1747.	3.3	41
24	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. Nature Physics, 2008, 4, 55-59.	16.7	39
25	$\nu = 5$ quantum Hall state in low-mobility electron systems: Different roles of disorder. Physical Review B, 2013, 88, .	3.2	38
26	Gate-controlled semimetal-topological insulator transition in an InAs/GaSb heterostructure. Physical Review B, 2015, 91, .	3.2	38
27	Electronic states in quantum dot atoms and molecules. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 3, 112-120.	2.7	37
28	Magnetic field induced transitions in the few-electron ground states of artificial molecules. Solid State Communications, 2001, 119, 183-190.	1.9	37
29	Exciton condensate at a total filling factor of one in Corbino two-dimensional electron bilayers. Physical Review B, 2008, 77, .	3.2	37
30	Distributed-element circuit model of edge magnetoplasmon transport. Physical Review B, 2013, 88, .	3.2	37
31	n+-GaAs Back-Gated Double-Quantum-Well Structures with Full Density Control. Japanese Journal of Applied Physics, 2000, 39, 2444-2447.	1.5	36
32	Spin-Dependent Phase Diagram of the $\nu = 1$ Bilayer Electron System. Physical Review Letters, 2008, 100, 106803.	7.8	36
33	Real-space imaging of fractional quantum Hall liquids. Nature Nanotechnology, 2013, 8, 31-35.	31.5	36
34	Electron-spin/nuclear-spin interactions and NMR in semiconductors. Semiconductor Science and Technology, 2009, 24, 023001.	2.0	34
35	Distributed electrochemical capacitance evidenced in high-frequency admittance measurements on a quantum Hall device. Physical Review B, 2012, 85, .	3.2	34
36	Fabrication of induced two-dimensional hole systems on (311)A GaAs. Journal of Applied Physics, 2006, 99, 023707.	2.5	30

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37	Spin-orbital Kondo effect in a parallel double quantum dot. Physical Review B, 2011, 84, .	3.2	30
38	Magnetic-Field Dependence of Tunnel Couplings in Carbon Nanotube Quantum Dots. Physical Review Letters, 2012, 108, 176802.	7.8	30
39	Shot noise spectroscopy on a semiconductor quantum dot in the elastic and inelastic cotunneling regimes. Physical Review B, 2013, 87, .	3.2	29
40	Single-edge transport in an InAs/GaSb quantum spin Hall insulator. Physical Review B, 2016, 94, .	3.2	29
41	Resistance fluctuations in quantum Hall transitions: Network of compressible-incompressible regions. Physical Review B, 2001, 63, .	3.2	26
42	Vertical diatomic artificial molecule in the intermediate-coupling regime in a parallel and perpendicular magnetic field. Physical Review B, 2003, 67, .	3.2	26
43	Impact of graphene quantum capacitance on transport spectroscopy. Physical Review B, 2012, 86, .	3.2	26
44	Signatures of a Nonthermal Metastable State in Copropagating Quantum Hall Edge Channels. Physical Review Letters, 2018, 120, 197701.	7.8	26
45	Nanometre-scale nuclear-spin device for quantum information processing. Journal of Physics Condensed Matter, 2006, 18, S885-S900.	1.8	25
46	Fabrication and characterization of an induced GaAs single hole transistor. Applied Physics Letters, 2010, 96, 092103.	3.3	25
47	Interlayer charge transfer in bilayer quantum Hall states at various filling factors. Solid State Communications, 1999, 112, 625-629.	1.9	24
48	Engineering quantum spin Hall insulators by strained-layer heterostructures. Applied Physics Letters, 2016, 109, .	3.3	24
49	The interplay between one-dimensional confinement and two-dimensional crystallographic anisotropy effects in ballistic hole quantum wires. New Journal of Physics, 2009, 11, 043018.	2.9	21
50	Bidirectional Current Drag Induced by Two-Electron Cotunneling in Coupled Double Quantum Dots. Applied Physics Express, 0, 2, 081101.	2.4	21
51	Phase Diagram of Interacting Composite Fermions in the Bilayer $\nu=2/3$ Quantum Hall Effect. Physical Review Letters, 2002, 89, 116802.	7.8	20
52	Gate-Dependent Orbital Magnetic Moments in Carbon Nanotubes. Physical Review Letters, 2011, 107, 186802.	7.8	20
53	Shot-Noise Evidence of Fractional Quasiparticle Creation in a Local Fractional Quantum Hall State. Physical Review Letters, 2015, 114, 056802.	7.8	20
54	Andreev reflection of fractional quantum Hall quasiparticles. Nature Communications, 2021, 12, 2794.	12.8	20

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55	Spectroscopic study on hot-electron transport in a quantum Hall edge channel. <i>Physical Review B</i> , 2019, 99, .	3.2	19
56	Observation of Hysteretic Transport due to Dynamic Nuclear Spin Polarization in a GaAs Lateral Double Quantum Dot. <i>Physical Review Letters</i> , 2011, 107, 216802.	7.8	18
57	Encapsulated gate-all-around InAs nanowire field-effect transistors. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	18
58	Detection and Control of Spin-Orbit Interactions in a GaAs Hole Quantum Point Contact. <i>Physical Review Letters</i> , 2017, 118, 146801.	7.8	18
59	Simultaneous excitation of spins and pseudospins in the bilayer $\nu=1$ quantum Hall state. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 52-55.	2.7	17
60	Intrinsic Gap and Exciton Condensation in the $\nu=1$ Bilayer System. <i>Physical Review Letters</i> , 2010, 104, 056802.	7.8	17
61	The infrared vibrational absorption spectrum of the Si ⁻ X defect present in heavily Si doped GaAs. <i>Journal of Applied Physics</i> , 1997, 82, 137-141.	2.5	16
62	Effects of Inversion Asymmetry on Electron-Nuclear Spin Coupling in Semiconductor Heterostructures: Possible Role of Spin-Orbit Interactions. <i>Physical Review Letters</i> , 2005, 94, 146601.	7.8	16
63	Two-dimensional exciton dynamics in InGaAs/GaAs quantum wells. <i>Applied Physics Letters</i> , 1992, 60, 213-215.	3.3	15
64	High-Mobility Two-Dimensional Electron Gas in an Undoped Heterostructure: Mobility Enhancement after Illumination. <i>Japanese Journal of Applied Physics</i> , 1998, 37, L765-L767.	1.5	15
65	Cross-correlation measurement of quantum shot noise using homemade transimpedance amplifiers. <i>Review of Scientific Instruments</i> , 2014, 85, 054704.	1.3	15
66	Long-lived binary tunneling spectrum in the quantum Hall Tomonaga-Luttinger liquid. <i>Physical Review B</i> , 2016, 93, .	3.2	15
67	Charge equilibration in integer and fractional quantum Hall edge channels in a generalized Hall-bar device. <i>Physical Review B</i> , 2019, 99, .	3.2	15
68	Anomalies in photoluminescence linewidth of InGaAs/GaAs strained-layer quantum wells. <i>Surface Science</i> , 1992, 267, 107-109.	1.9	14
69	Doubly Enhanced Skyrmions in $\nu=2$ Bilayer Quantum Hall States. <i>Journal of the Physical Society of Japan</i> , 2000, 69, 3178-3181.	1.6	14
70	Phase diagrams of $\nu=2$ and $\nu=3$ quantum Hall states in bilayer systems. <i>Physical Review B</i> , 2004, 69, .	3.2	14
71	Electronic transport characteristics in a one-dimensional constriction defined by a triple-gate structure. <i>Journal of Applied Physics</i> , 2006, 100, 043701.	2.5	14
72	Probing the extended-state width of disorder-broadened Landau levels in epitaxial graphene. <i>Physical Review B</i> , 2015, 92, .	3.2	14

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73	Enhanced electron-phonon coupling for a semiconductor charge qubit in a surface phonon cavity. <i>Scientific Reports</i> , 2015, 5, 15176.	3.3	14
74	Time-of-flight measurement of carrier transport and carrier collection in strained Si $_{1-x}$ Ge $_x$ /Si quantum wells. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994, 12, 1156.	1.6	13
75	Coulomb Drag as a Probe of the Nature of Compressible States in a Magnetic Field. <i>Physical Review Letters</i> , 2004, 92, 246801.	7.8	13
76	Integer filling factor phases and isospin in vertical diatomic artificial molecules. <i>Physical Review B</i> , 2004, 70, .	3.2	13
77	Charge fractionalization in artificial Tomonaga-Luttinger liquids with controlled interaction strength. <i>Physical Review B</i> , 2017, 96, .	3.2	13
78	Energy gap tuning and gate-controlled topological phase transition in $\text{InAs}/\text{AlGaSb}$ composite quantum wells. <i>Physical Review Materials</i> , 2020, 4, .	2.1	13
79	Longitudinal resistance anomaly around the 2/3 filling factor observed in a GaAs/AlGaAs single heterostructure. <i>Physica B: Condensed Matter</i> , 2001, 298, 191-194.	2.7	12
80	Modulation of bilayer quantum Hall states by tilted-field-induced subband-Landau-level coupling. <i>Physical Review B</i> , 2008, 77, .	3.2	12
81	Gate Operation of InAs/AlGaSb Heterostructures with an Atomic-Layer-Deposited Insulating Layer. <i>Applied Physics Express</i> , 2011, 4, 125702.	2.4	12
82	Intrinsic and extrinsic origins of low-frequency noise in GaAs/AlGaAs Schottky-gated nanostructures. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	12
83	NMR probing of spin and charge order near odd-integer filling in the second Landau level. <i>Physical Review B</i> , 2015, 92, .	3.2	12
84	Electrical control of the sign of the g factor in a GaAs hole quantum point contact. <i>Physical Review B</i> , 2016, 94, .	3.2	12
85	Quantized charge fractionalization at quantum Hall Y junctions in the disorder dominated regime. <i>Nature Communications</i> , 2021, 12, 131.	12.8	12
86	Fast Lateral Transport of Excitons in a GaAs/AlGaAs Quantum Well. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 5586-5590.	1.5	11
87	Spin transition of a two-dimensional hole system in the fractional quantum Hall effect. <i>Physical Review B</i> , 1999, 59, R2502-R2505.	3.2	11
88	Wide-band capacitance measurement on a semiconductor double quantum dot for studying tunneling dynamics. <i>Applied Physics Letters</i> , 2010, 96, 032104.	3.3	11
89	Evaluation of disorder introduced by electrolyte gating through transport measurements in graphene. <i>Applied Physics Express</i> , 2016, 9, 065102.	2.4	11
90	Landau-Zener-Stückelberg interference in coherent charge oscillations of a one-electron double quantum dot. <i>Scientific Reports</i> , 2018, 8, 5491.	3.3	11

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91	In-plane transport of excitons in quantum well structures. Solid State Communications, 1993, 88, 677-681.	1.9	10
92	Direct observation of exciton localization in a GaAs/AlGaAs quantum well. Applied Physics Letters, 1994, 64, 1845-1847.	3.3	10
93	Growth of InGaAs/GaAs strained quantum wells on GaAs(111)B substrates and continuous wave operation of (111)-oriented InGaAs strained quantum well lasers. Journal of Crystal Growth, 1995, 150, 1338-1343.	1.5	10
94	Splitting of resistance peaks and anomalous Hall plateaus in asymmetric double-quantum-well structures. Physical Review B, 1997, 56, 1057-1060.	3.2	10
95	Single dot and strongly coupled double dots at high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 112-116.	2.7	10
96	Continuous transformation from spin- to pseudospin-type excitation. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 18, 118-119.	2.7	10
97	Self-sustaining resistance oscillations: Electron-nuclear spin coupling in mesoscopic quantum Hall devices. Physical Review B, 2004, 69, .	3.2	10
98	The 0.7 anomaly in one-dimensional hole quantum wires. Journal of Physics Condensed Matter, 2008, 20, 164205.	1.8	10
99	Plasmon transport and its guiding in graphene. New Journal of Physics, 2014, 16, 063055.	2.9	10
100	Counterflowing edge current and its equilibration in quantum Hall devices with sharp edge potential: Roles of incompressible strips and contact configuration. Physical Review B, 2019, 99, .	3.2	10
101	Electrons and holes in a 40 nm thick silicon slab at cryogenic temperatures. Applied Physics Letters, 2009, 94, 142104.	3.3	9
102	On-chip coherent frequency-domain THz spectroscopy for electrical transport. Applied Physics Letters, 2020, 117, .	3.3	9
103	Enhancement of nonradiative recombination due to resonant electron capture in $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum-well structures. Physical Review B, 1995, 51, 14324-14329.	3.2	8
104	Chaos and open orbits in hole-antidot arrays with non-isotropic Fermi surface. Europhysics Letters, 2003, 61, 382-388.	2.0	8
105	Highly reproducible fabrication of back-gated GaAs/AlGaAs heterostructures using AuGeNi ohmic contacts with initial Ni layer. Applied Physics Letters, 2008, 92, .	3.3	8
106	Impact of Valley Polarization on the Resistivity in Two Dimensions. Physical Review Letters, 2011, 106, 196403.	7.8	8
107	Evidence for resonant electron capture and charge buildup in $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells. Physical Review B, 1996, 53, 15477-15480.	3.2	7
108	Nonequilibrium population in fractional edge states. Physica B: Condensed Matter, 2001, 298, 150-154.	2.7	7

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109	Activation studies of pseudospin quantum Hall ferromagnets in double quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 8-11.	2.7	7
110	Determination of g -factor in InAs two-dimensional electron system by capacitance spectroscopy. <i>Applied Physics Express</i> , 2019, 12, 063004.	2.4	7
111	Observation of the valence subband level crossing in GaAs/GaAsP strained barrier quantum well structures using circularly polarized photoluminescence excitation spectroscopy. <i>Applied Physics Letters</i> , 1993, 63, 946-948.	3.3	6
112	Enhancement of free-to-bound transitions due to resonant electron capture in Be-doped AlGaAs/GaAs quantum wells. <i>Solid-State Electronics</i> , 1994, 37, 1247-1250.	1.4	6
113	Suppression of superlattice intermixing by p-type doping. <i>Journal of Crystal Growth</i> , 1997, 175-176, 162-167.	1.5	6
114	Spin-dependent tunneling rates for electrostatically defined GaAs quantum dots. <i>Physical Review B</i> , 2014, 90, .	3.2	6
115	Negative and positive cross-correlations of current noises in quantum Hall edge channels at bulk filling factor $\nu = 1$. <i>Journal of Physics Condensed Matter</i> , 2017, 29, 225302.	1.8	6
116	Two-electron double quantum dot coupled to coherent photon and phonon fields. <i>Physical Review B</i> , 2017, 96, .	3.2	6
117	Ballistic hot-electron transport in a quantum Hall edge channel defined by a double gate. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	6
118	Suppression of gate screening on edge magnetoplasmons by highly resistive ZnO gate. <i>Physical Review B</i> , 2020, 101, .	3.2	6
119	Screening Effects of Superlattice Doping on the Mobility of GaAs Two-Dimensional Electron System Revealed by in situ Gate Control. <i>Physical Review Applied</i> , 2021, 15, .	3.8	6
120	Effect of valence band structure on the fractional quantum Hall effect of two-dimensional hole systems. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 65-69.	2.7	5
121	Self-aligned gate-all-around InAs/InP core-shell nanowire field-effect transistors. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DN04.	1.5	5
122	Observation of spatially-indirect transition and accurate determination of band offset ratio by excitation spectroscopy on GaAs/AlGaAs quantum wells lightly doped with Be acceptors. <i>Journal of Crystal Growth</i> , 1995, 150, 49-53.	1.5	4
123	Quantum Hall effects at Landau level crossings. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 20, 133-142.	2.7	4
124	ANISOTROPIC TRANSPORT ON THE $\nu = 1$ BILAYER QUANTUM HALL SYSTEM UNDER TILTED MAGNETIC FIELD. <i>International Journal of Modern Physics B</i> , 2004, 18, 3705-3708.	2.0	4
125	Investigating the transport properties of the excitonic state in quasi-Corbino electron bilayers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1034-1037.	2.7	4
126	Interferometric detection of edge magnetoplasmons in AlGaAs/GaAs heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 381-383.	0.8	4

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127	Frequency conversion of radio-frequency edge magnetoplasmons using a quantum point contact. Applied Physics Letters, 2012, 100, 233501.	3.3	4
128	Stable and unstable dynamics of Overhauser fields in a double quantum dot. Physical Review B, 2014, 89, .	3.2	4
129	Single-electron counting statistics with a finite frequency bandwidth. Japanese Journal of Applied Physics, 2014, 53, 04EJ01.	1.5	4
130	Two-step breakdown of a local $\nu=1$ quantum Hall state. Physical Review B, 2020, 101, .	3.2	4
131	Cryogenic GaAs high-electron-mobility-transistor amplifier for current noise measurements. Review of Scientific Instruments, 2021, 92, 023910.	1.3	4
132	Time-resolved investigation of plasmon mode along interface channels in integer and fractional quantum Hall regimes. Physical Review B, 2021, 104, .	3.2	4
133	Quantum Hall effect in asymmetric double quantum well systems. Semiconductor Science and Technology, 1998, 13, 296-301.	2.0	3
134	Photoluminescence from a modulation-doped Al _{0.33} Ga _{0.67} As/GaAs heterointerface under cyclotron resonance. Physical Review B, 1998, 58, 15385-15388.	3.2	3
135	Density functional theory application to double quantum dots: Influence of mismatch on the addition energy spectra of vertical diatomic artificial molecules. International Journal of Quantum Chemistry, 2003, 91, 498-503.	2.0	3
136	Nuclear-spin-lattice relaxation in a bilayer quantum Hall system. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 164-167.	2.7	3
137	Time Resolved Potential Measurement At Quantum Point Contacts Under Irradiation Of Surface Acoustic Burst Wave. , 2011, , .		3
138	Admittance Measurement for a Quantum Point Contact in a Multiterminal Quantum Hall Device. Japanese Journal of Applied Physics, 2011, 50, 04DJ04.	1.5	3
139	Coupling between quantum Hall edge channels on opposite sides of a Hall bar. Solid State Communications, 2018, 283, 32-36.	1.9	3
140	Surface-acoustic-wave resonators with Ti, Cr, and Au metallization on GaAs. Applied Physics Express, 2019, 12, 055001.	2.4	3
141	Impact of epitaxial strain on the topological-nontopological phase diagram and semimetallic behavior of InAs/GaSb composite quantum wells. Physical Review B, 2020, 101, .	3.2	3
142	Metastability of the quantum Hall states in asymmetric two-layer systems. Journal of Physics Condensed Matter, 1998, 10, 8305-8311.	1.8	2
143	Resistance fluctuations in integer quantum-Hall transitions. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 152-155.	2.7	2
144	Spin polarization in fractional quantum Hall edge channels. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 76-79.	2.7	2

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145	Influence of mismatch on the addition energy spectra of vertical diatomic artificial molecules. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 896-899.	2.7	2
146	Intralayer backscattering in narrow GaAs/Al _x Ga _{1-x} As/GaAs bilayer channels. <i>Physical Review B</i> , 2004, 69, .	3.2	2
147	DOUBLE MAGNETORESISTANCE MINIMA INDUCED BY THE IN-PLANE MAGNETIC FIELD FOR THE $\nu=1$ DOUBLE-LAYER QUANTUM HALL STATE. <i>International Journal of Modern Physics B</i> , 2004, 18, 3709-3712.	2.0	2
148	Effects of in-plane magnetic fields on spin transitions in bilayer quantum Hall states. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 36-39.	2.7	2
149	Fabrication and characterization of a 2D hole system in a novel (311)A GaAs SISFET. <i>Microelectronics Journal</i> , 2005, 36, 327-330.	2.0	2
150	Exchange-Induced Spin Blockade in a Two-Electron Double Quantum Dot. <i>Physical Review Letters</i> , 2015, 115, 176802.	7.8	2
151	Dissipative Landau-Zener transition in double quantum dot under sinusoidal potential modulation. <i>Applied Physics Express</i> , 2017, 10, 115201.	2.4	2
152	Generation and detection of edge magnetoplasmons in a quantum Hall system using a photoconductive switch. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 04FK02.	1.5	2
153	Electronic energy spectroscopy of monochromatic edge magnetoplasmons in the quantum Hall regime. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 345301.	1.8	2
154	Gate tuning of fractional quantum Hall states in an InAs two-dimensional electron gas. <i>Physical Review B</i> , 2022, 105, .	3.2	2
155	Homemade-HEMT-based transimpedance amplifier for high-resolution shot-noise measurements. <i>Review of Scientific Instruments</i> , 2021, 92, 124712.	1.3	2
156	Re-entrant behavior of the $\nu=4/3$ fractional quantum Hall effect in a front-and-back-gated 2D hole gas. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 86-89.	2.7	1
157	Backgated layers and nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 11, 155-160.	2.7	1
158	Various phase transitions in bilayer quantum Hall states. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 32-35.	2.7	1
159	Electron Nuclear Spin Interaction in Edge States of Quantum Hall Systems. <i>Journal of the Physical Society of Japan</i> , 2003, 72, 44-48.	1.6	1
160	NMR study of a canted antiferromagnet in a bilayer quantum Hall system. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 937-941.	2.7	1
161	Quantum transport in one-dimensional GaAs hole systems. <i>International Journal of Nanotechnology</i> , 2008, 5, 318.	0.2	1
162	SPIN EFFECTS IN THE PHASE TRANSITION OF THE $\nu_{T=1}$ BILAYER ELECTRON SYSTEM. <i>International Journal of Modern Physics B</i> , 2009, 23, 2587-2595.	2.0	1

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163	Low-temperature scanning tunneling microscopy of self-assembled InAs quantum dots grown by droplet epitaxy. <i>Physics Procedia</i> , 2010, 3, 1299-1304.	1.2	1
164	Density-Imbalance Stability Diagram of the $\nu = 1$ Bilayer Electron System at Full Spin Polarization. <i>Journal of Physics: Conference Series</i> , 2011, 334, 012025.	0.4	1
165	Correlation of $1/f$ Noise between Semiconductor Point Contacts with a Common Lead. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 02BJ08.	1.5	1
166	Transient Current in the Spin Blockade Region of a Double Quantum Dot. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 110204.	1.5	1
167	Andreev reflection and bound state formation in a ballistic two-dimensional electron gas probed by a quantum point contact. <i>Physical Review B</i> , 2016, 94, .	3.2	1
168	Sensitive current measurement on a quantum antidot with a Corbino-type electrode. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SGGI03.	1.5	1
169	Transport Spectroscopy of Epitaxial Graphene on SiC Using Quantum Capacitances. , 2014, , .		1
170	Admittance Measurement for a Quantum Point Contact in a Multiterminal Quantum Hall Device. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DJ04.	1.5	1
171	n-GaAs Back-Gated Double-Quantum-Well Structures with Full Density Control. , 1999, , .		1
172	Nonuniform heat redistribution among multiple channels in the integer quantum Hall regime. <i>Physical Review B</i> , 2022, 105, .	3.2	1
173	Valence-subband level crossing in GaAs/GaAsP strained-barrier quantum well structures observed by circularly polarized photoluminescence excitation spectroscopy. <i>Solid-State Electronics</i> , 1994, 37, 915-918.	1.4	0
174	High-quality two-dimensional electron gas at an inverted undoped heterointerface. <i>Superlattices and Microstructures</i> , 1999, 25, 295-300.	3.1	0
175	Quantum coherence and skyrmion textures in bilayer quantum Hall systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 640-644.	2.7	0
176	Preferred number of flipped spins in Skyrmion excitation. <i>Physica B: Condensed Matter</i> , 2001, 298, 169-172.	2.7	0
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